NGTB20N120IHLWG

IGBT

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on−state voltage and minimal switching loss. The IGBT is well suited for resonant or soft switching applications. Incorporated into the device is a rugged co−packaged free wheeling diode with a low forward voltage.

Features

- Low Saturation Voltage using Trench with Fieldstop Technology
- Low Switching Loss Reduces System Power Dissipation
- Optimized for Low Case Temperature in IH Cooker Application
- Low Gate Charge
- These are Pb−Free Devices

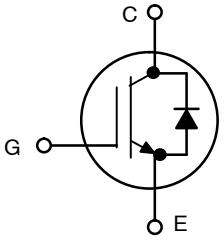
Typical Applications

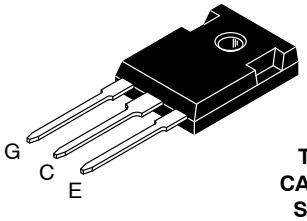
- Inductive Heating
- Consumer Appliances
- Soft Switching

ON Semiconductor®

http://onsemi.com

20 A, 1200 V
V_{CEsat} = 1.80 V
E_{off} = 0.7 mJ





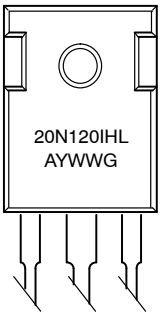
TO−247
CASE 340L
STYLE 4

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−emitter voltage	V_{CES}	1200	V
Collector current @ T_C = 25°C @ T_C = 100°C	I_C	 40 20	A
Pulsed collector current, T_{pulse} limited by T_{Jmax}	I_{CM}	200	A
Diode forward current @ T_C = 25°C @ T_C = 100°C	I_F	 40 20	A
Diode pulsed current, T_{pulse} limited by T_{Jmax}	I_{FM}	200	A
Gate−emitter voltage	V_{GE}	±20	V
Power Dissipation @ T_C = 25°C @ T_C = 100°C	P_D	 192 77	W
Operating junction temperature range	T_J	−55 to +150	°C
Storage temperature range	T_{stg}	−55 to +150	°C
Lead temperature for soldering, 1/8” from case for 5 seconds	T_{SLD}	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTB20N120IHLWG	TO−247 (Pb−Free)	30 Units / Rail

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction−to−case, for IGBT	$R_{\theta JC}$	0.65	°C/W
Thermal resistance junction−to−case, for Diode	$R_{\theta JC}$	2.0	°C/W
Thermal resistance junction−to−ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
STATIC CHARACTERISTIC						
Collector−emitter breakdown voltage, gate−emitter short−circuited	V_{GE} = 0 V, I_C = 500 μA	$V_{(BR)CES}$	1200	−	−	V
Collector−emitter saturation voltage	V_{GE} = 15 V, I_C = 20 A V_{GE} = 15 V, I_C = 20 A, T_J = 150°C	V_{CEsat}	− −	1.80 2.0	2.2 −	V
Gate−emitter threshold voltage	V_{GE} = V_{CE}, I_C = 250 μA	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector−emitter cut−off current, gate−emitter short−circuited	V_{GE} = 0 V, V_{CE} = 1200 V V_{GE} = 0 V, V_{CE} = 1200 V, T_J = 150°C	I_{CES}	− −	− −	0.5 2.0	mA
Gate leakage current, collector−emitter short−circuited	V_{GE} = 20 V, V_{CE} = 0 V	I_{GES}	−	−	100	nA
DYNAMIC CHARACTERISTIC						
Input capacitance	V_{CE} = 20 V, V_{GE} = 0 V, f = 1 MHz	C_{ies}	−	4700	−	pF
Output capacitance		C_{oes}	−	155	−	
Reverse transfer capacitance		C_{res}	−	100	−	
Gate charge total	V_{CE} = 600 V, I_C = 20 A, V_{GE} = 15 V	Q_g		200		nC
Gate to emitter charge		Q_{ge}		36		
Gate to collector charge		Q_{gc}		98		
SWITCHING CHARACTERISTIC, INDUCTIVE LOAD						
Turn−off delay time	T_J = 25°C V_{CC} = 600 V, I_C = 20 A R_g = 10 Ω V_{GE} = 0 V/ 15V	$t_{d(off)}$		235		ns
Fall time		t_f		180		
Turn−off switching loss		E_{off}		0.7		mJ
Turn−off delay time	T_J = 125°C V_{CC} = 600 V, I_C = 20 A R_g = 10 Ω V_{GE} = 0 V/ 15V	$t_{d(off)}$		235		ns
Fall time		t_f		250		
Turn−off switching loss		E_{off}		1.60		mJ
DIODE CHARACTERISTIC						
Forward voltage	V_{GE} = 0 V, I_F = 20 A V_{GE} = 0 V, I_F = 20 A, T_J = 150°C	V_F		1.55 1.65	1.75	V

TYPICAL CHARACTERISTICS

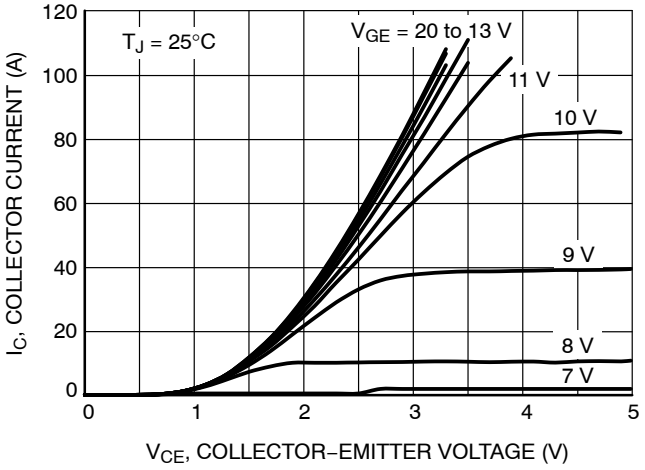


Figure 1. Output Characteristics

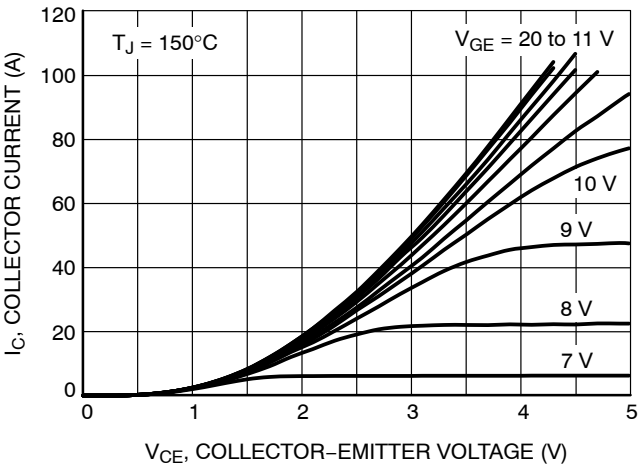


Figure 2. Output Characteristics

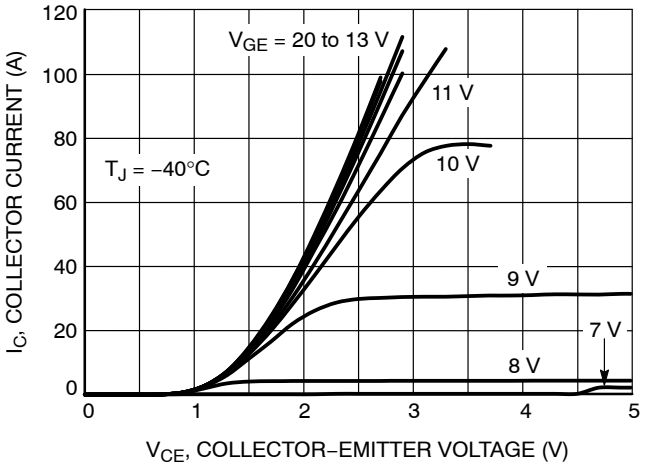


Figure 3. Output Characteristics

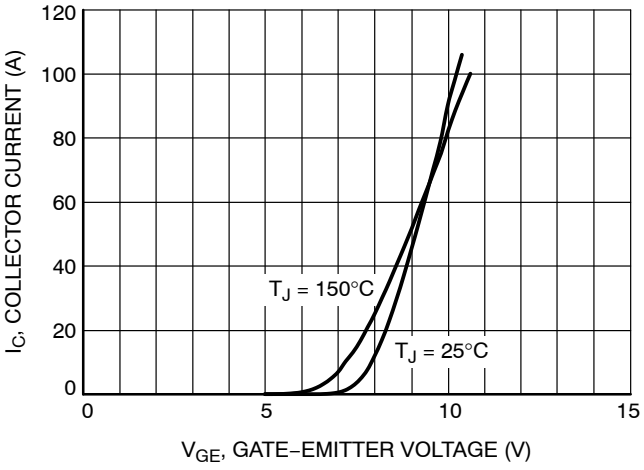


Figure 4. Typical Transfer Characteristics

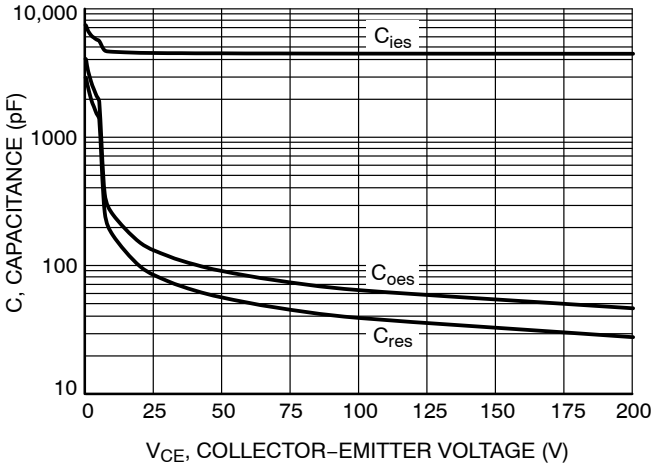


Figure 5. Typical Capacitance

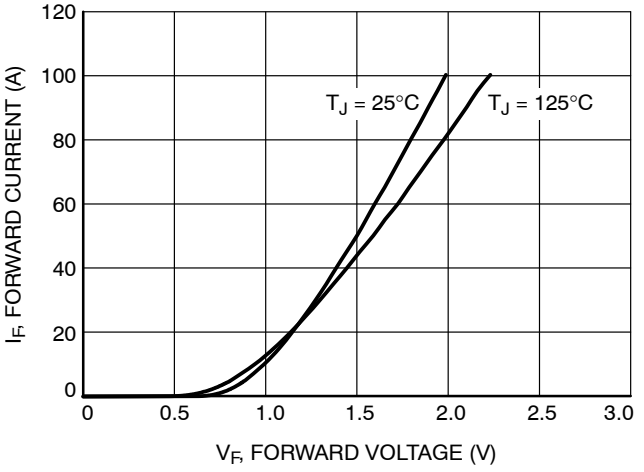


Figure 6. Diode Forward Characteristics

TYPICAL CHARACTERISTICS

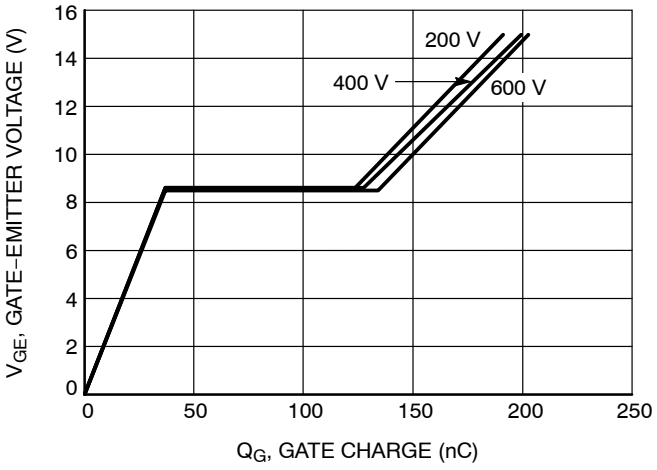


Figure 7. Typical Gate Charge

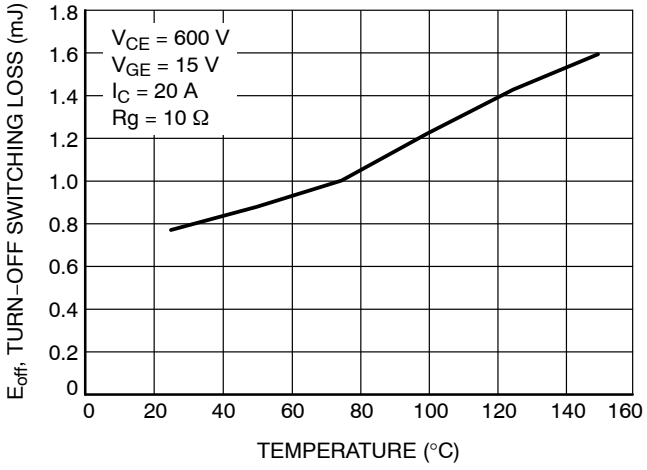


Figure 8. Energy Loss vs. Temperature

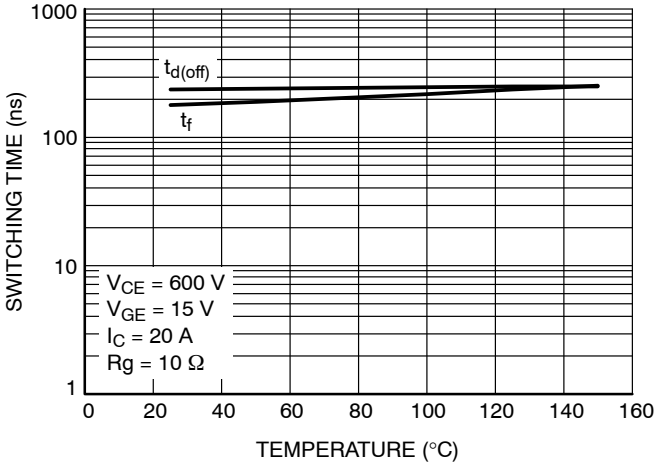


Figure 9. Switching Time vs. Temperature

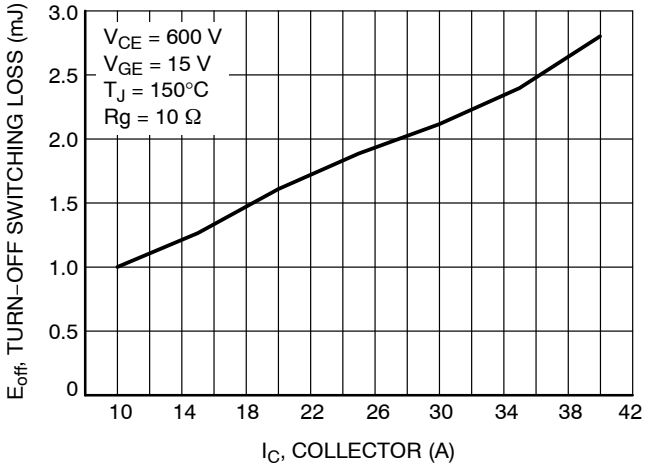


Figure 10. Energy Loss vs. I_C

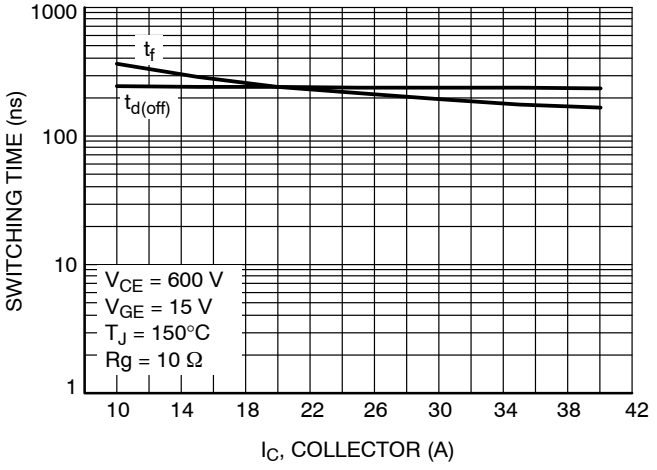


Figure 11. Switching Time vs. I_C

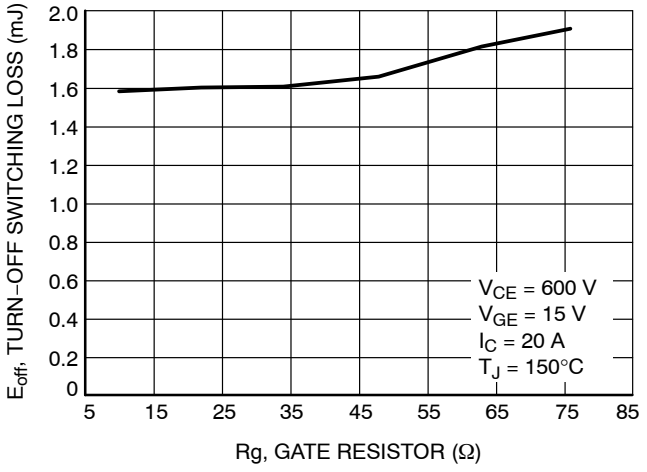


Figure 12. Energy Loss vs. Rg

TYPICAL CHARACTERISTICS

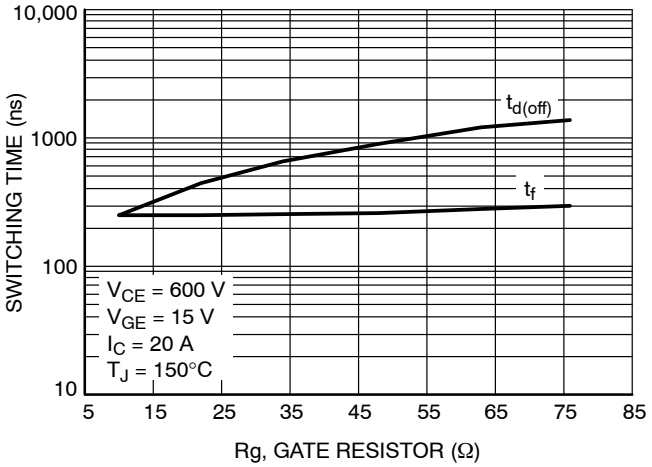


Figure 13. Switching Time vs. Rg

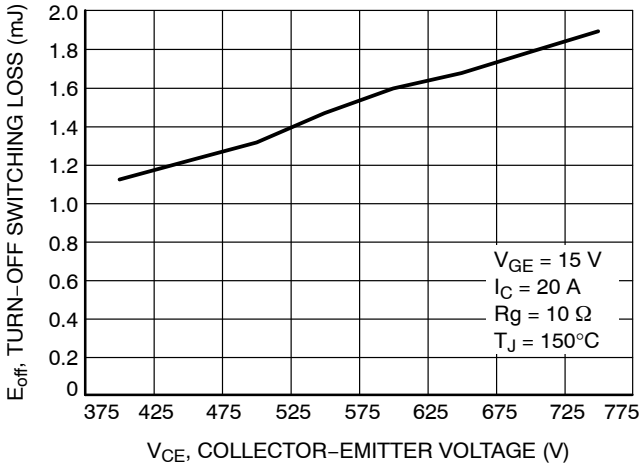


Figure 14. Energy Loss vs. V_{CE}

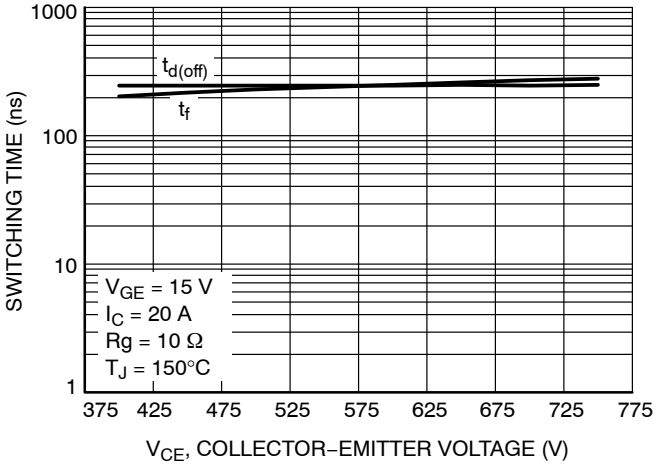


Figure 15. Switching Time vs. V_{CE}

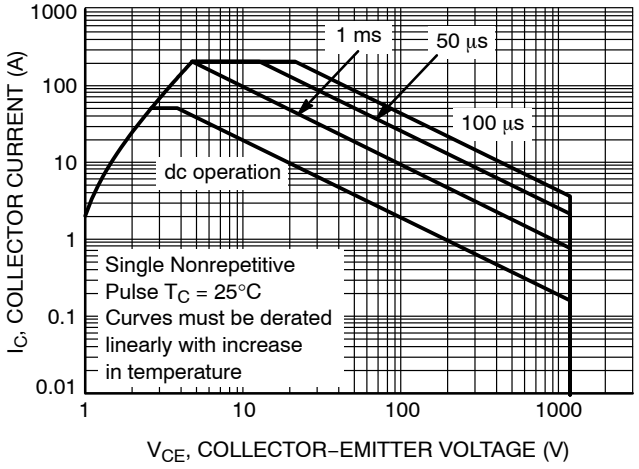


Figure 16. Safe Operating Area

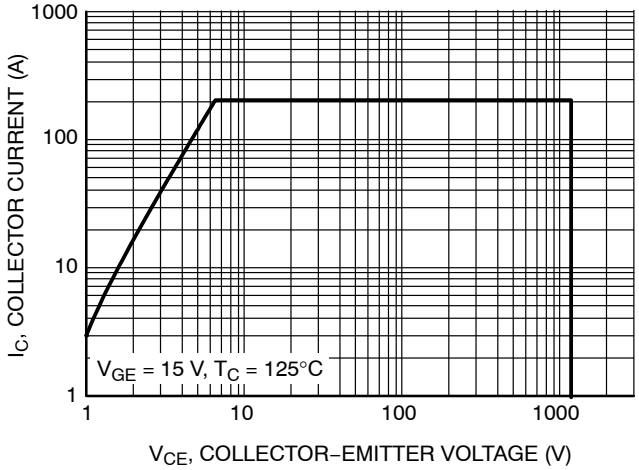
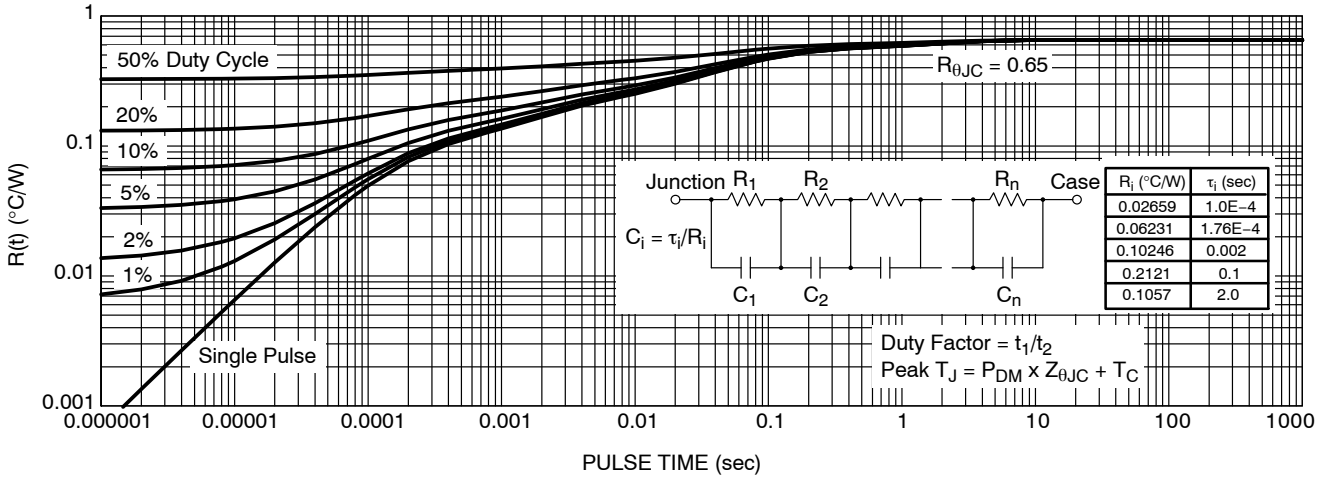


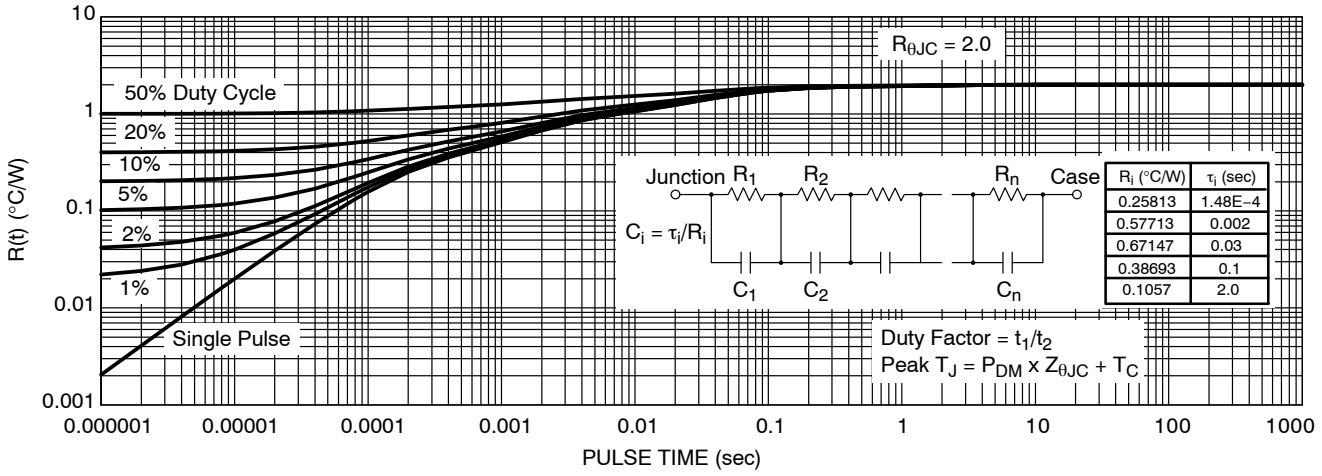
Figure 17. Reverse Bias Safe Operating Area

TYPICAL CHARACTERISTICS



R_i (°C/W)	τ_i (sec)
0.02659	1.0E−4
0.06231	1.76E−4
0.10246	0.002
0.2121	0.1
0.1057	2.0

Figure 18. IGBT Transient Thermal Impedance



R_i (°C/W)	τ_i (sec)
0.25813	1.48E−4
0.57713	0.002
0.67147	0.03
0.38693	0.1
0.1057	2.0

Figure 19. Diode Transient Thermal Impedance

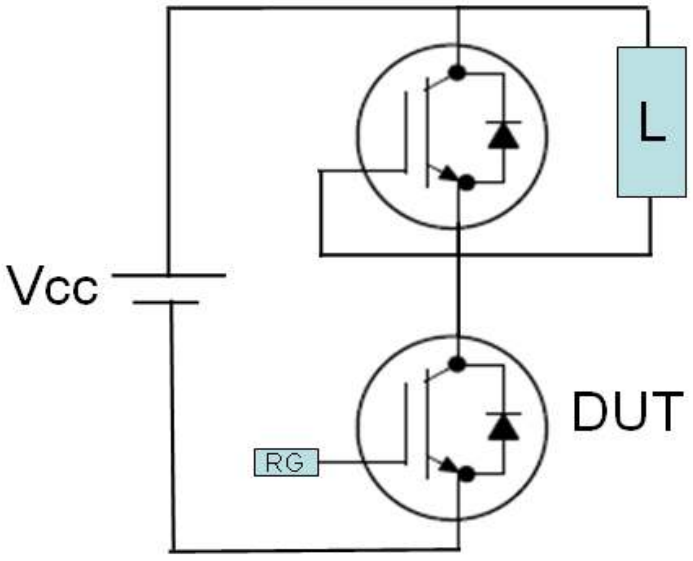


Figure 20. Test Circuit for Switching Characteristics

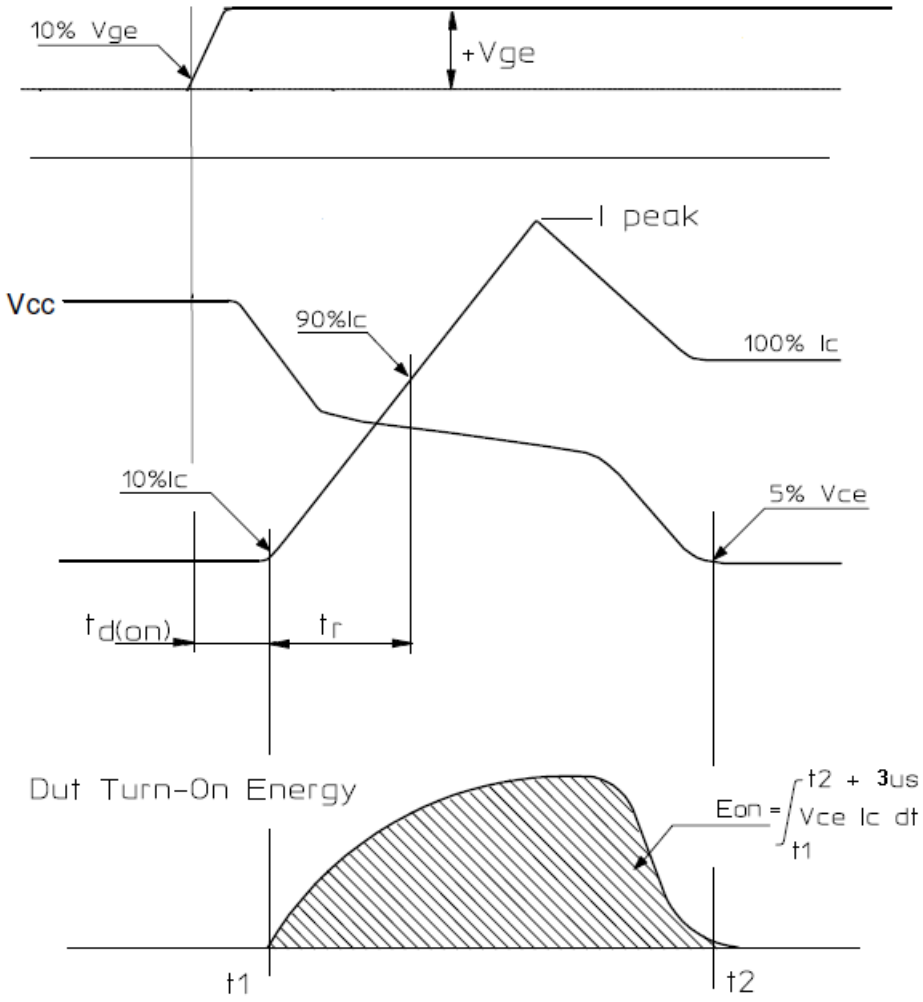


Figure 21. Definition of Turn On Waveform

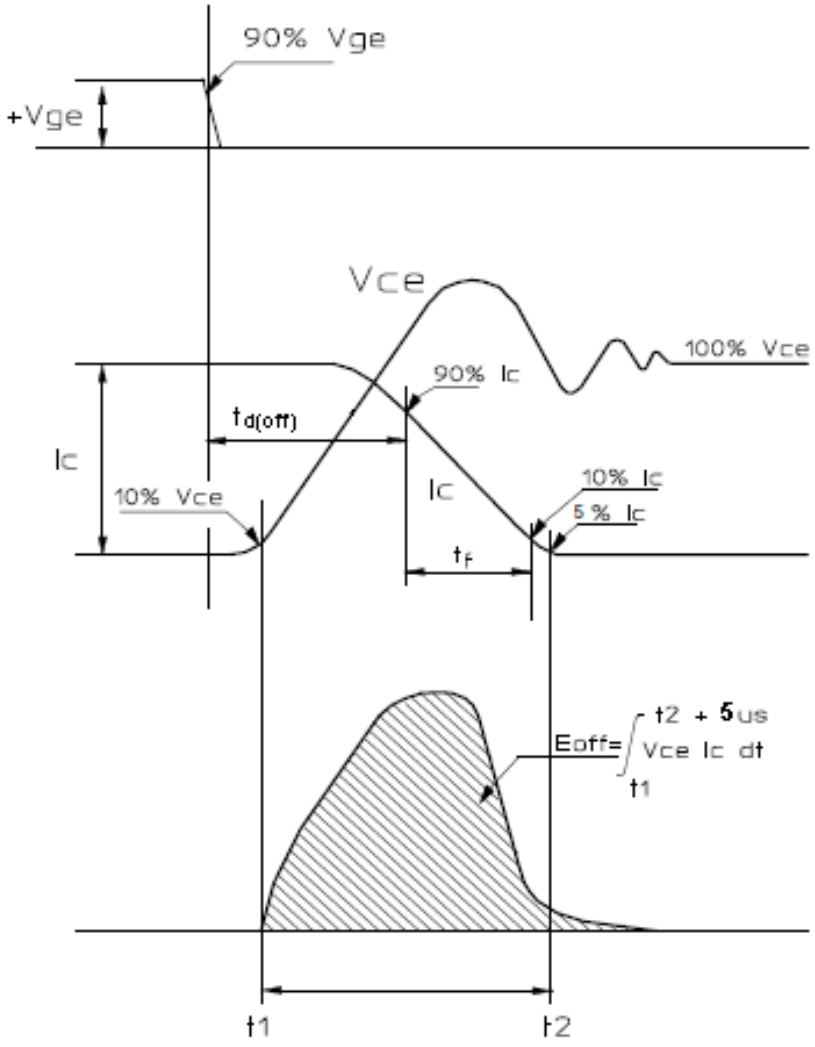
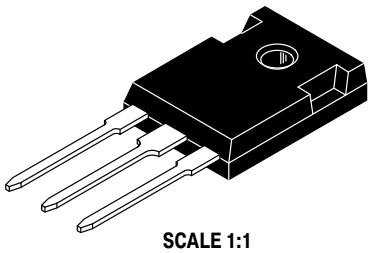


Figure 22. Definition of Turn Off Waveform

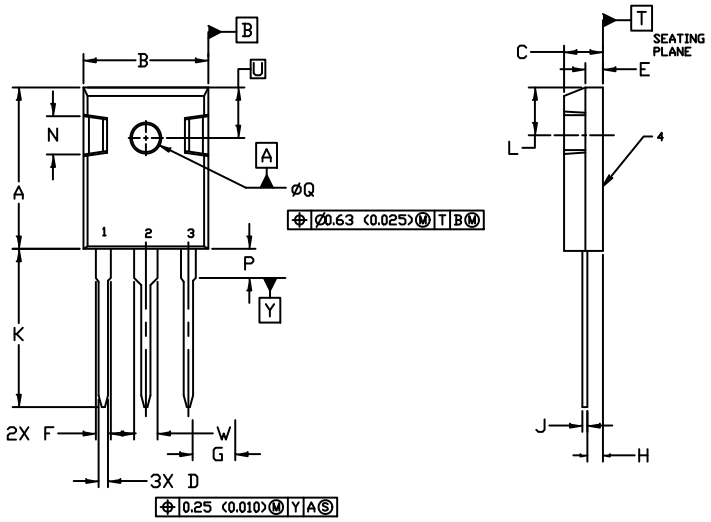
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

TO−247
CASE 340L
ISSUE G

DATE 06 OCT 2021



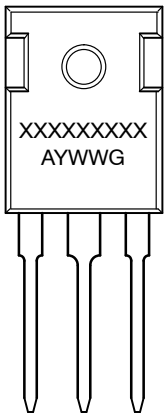
SCALE 1:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER

	MILLIMETERS		INCHES	
DIM	MIN.	MAX.	MIN.	MAX.
A	20.32	21.08	0.800	0.830
B	15.75	16.26	0.620	0.640
C	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
E	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45 BSC		0.215 BSC	
H	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
P	----	4.50	----	0.177
Q	3.55	3.65	0.140	0.144
U	6.15 BSC		0.242 BSC	
W	2.87	3.12	0.113	0.123

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 2:
PIN 1. ANODE
2. CATHODE (S)
3. ANODE 2
4. CATHODES (S)

STYLE 3:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 4:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE

STYLE 6:
PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

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DESCRIPTION:	**TO−247**	**PAGE 1 OF 1**

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